74AHC164-Q100; 74AHCT164-Q100

8-bit serial-in/parallel-out shift register

Rev. 1 — 5 July 2013

Product data sheet

1. General description

The 74AHC164-Q100; 74AHCT164-Q100 shift register is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard No. 7A.

The 74AHC164-Q100; 74AHCT164-Q100 input signals are 8-bit serial through one of two inputs (DSA or DSB). Either input can be used as an active HIGH enable for data entry through the other input. Both inputs must be connected together or an unused input must be tied HIGH.

Data shifts one place to the right on each LOW-to-HIGH transition of the clock input (CP). It enters into output Q0, which is a logical AND of the two data inputs (DSA and DSB). These data inputs existed one set-up time, prior to the rising clock edge.

A LOW-level on the master reset (\overline{MR}) input overrides all other inputs and clears the register asynchronously, forcing all outputs LOW.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ For 74AHC164-Q100: CMOS level
 - ◆ For 74AHCT164-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - ♦ MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

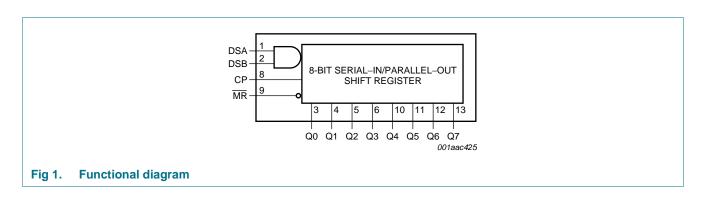


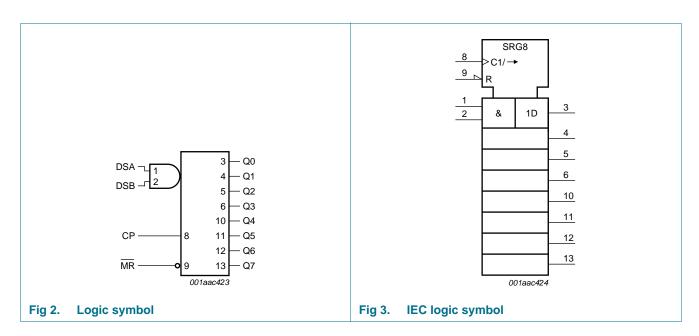
3. Ordering information

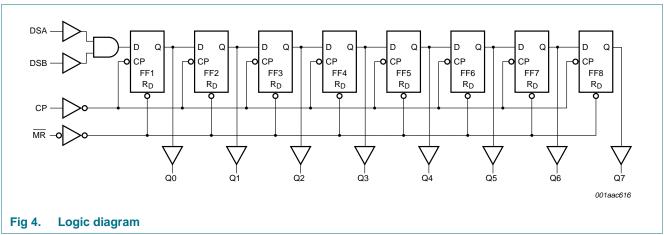
Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AHC164-Q100				
74AHC164D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHC164PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHC164BQ-Q100	–40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1
74AHCT164-Q100				
74AHCT164D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74AHCT164PW-Q100	-40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74AHCT164BQ-Q100	−40 °C to +125 °C	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85$ mm	SOT762-1

4. Functional diagram

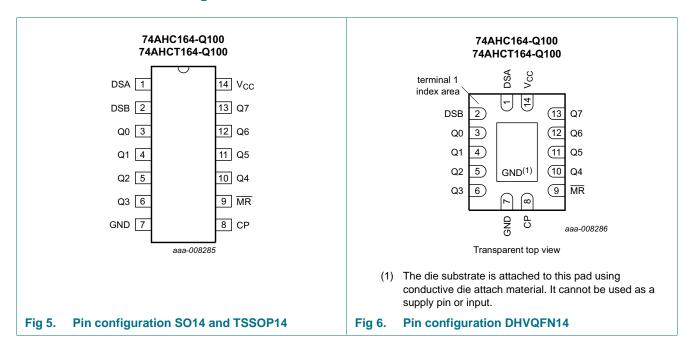






5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Table 2. Till des	scription	
Symbol	Pin	Description
DSA	1	serial data input A
DSB	2	serial data input B
Q0	3	output 0
Q1	4	output 1
Q2	5	output 2
Q3	6	output 3
GND	7	ground (0 V)
СР	8	clock input (LOW-to-HIGH edge-triggered)
MR	9	master reset input (active LOW)
Q4	10	output 4
Q5	11	output 5
Q6	12	output 6
Q7	13	output 7
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table[1]

Operating mode	Control		Input		Output	Output		
	MR	СР	DSA	DSB	Q0	Q1 to Q7		
Reset (clear)	L	X	X	X	L	L to L		
Shift	Н	↑	I	I	L	q0 to q6		
			I	h	L	q0 to q6		
			h	I	L	q0 to q6		
			h	h	Н	q0 to q6		

^[1] H = HIGH voltage level;

h = HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition;

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
VI	input voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_1 < -0.5 V$	<u>[1]</u> –20	-	mA
I _{OK}	output clamping current	$V_O < -0.5 \text{ V or } V_O > V_{CC} + 0.5 \text{ V}$	<u>[1]</u> –20	+20	mA
Io	output current	$V_{O} = -0.5 \text{ V to } (V_{CC} + 0.5 \text{ V})$	-25	+25	mA
I _{CC}	supply current		-	+75	mA
I_{GND}	ground current		−75	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] -	500	mW

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

For TSSOP14 packages: above 60 $^{\circ}\text{C}$ the value of P $_{tot}$ derates linearly at 5.5 mW/K.

For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

L = LOW voltage level;

I = LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition;

^{↑ =} LOW-to-HIGH transition;

X = don't care;

q = lower case letter indicates the state of the referenced input one set-up time prior to the LOW-to-HIGH transition.

^[2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

idbic o.	operating conditions					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
74AHC16	4-Q100					
V _{CC}	supply voltage		2.0	5.0	5.5	V
V_{I}	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	-	-	100	ns/V
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V
74AHCT1	64-Q100					
V _{CC}	supply voltage		4.5	5.0	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage		0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
74AHC1	64-Q100			•				1	1	
V _{IH}	HIGH-level	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V
	input voltage	V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V
V_{IL}	LOW-level	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V
	input voltage	V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V
	HIGH-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_{O} = -50 \mu A$; $V_{CC} = 2.0 \text{ V}$	1.9	2.0	-	1.9	-	1.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 3.0 \text{ V}$	2.9	3.0	-	2.9	-	2.9	-	V
		$I_O = -50 \mu A$; $V_{CC} = 4.5 \text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.58	-	-	2.48	-	2.40	-	V
		$I_{O} = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL}								
	output voltage	$I_O = 50 \mu A; V_{CC} = 2.0 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 3.0 \text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 50 \mu A; V_{CC} = 4.5 V$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	-	0.44	-	0.55	V
		I_{O} = 8.0 mA; V_{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V

74AHC_AHCT164_Q100

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 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		-40 °C 1	to +85 °C	-40 °C to +125 °C		Unit
			Min	Тур	Max	Min	Max	Min	Max	
l _l	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μΑ
C _I	input capacitance		-	3	10	-	-	-	-	pF
74AHCT	164-Q100									
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	2.0	-	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	-	-	8.0	-	0.8	-	0.8	V
V _{OH} HIGH-	HIGH-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	$I_{O} = -50 \ \mu A$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_0 = -8.0 \text{ mA}$	3.94	-	-	3.80	-	3.70	-	V
V_{OL}	LOW-level	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 50 μA	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 8.0 \text{ mA}$	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	$V_I = 5.5 \text{ V or GND};$ $V_{CC} = 0 \text{ V to 5.5 V}$	-	-	0.1	-	1.0	-	2.0	μΑ
I _{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5 \text{ V}$	-	-	4.0	-	40	-	80	μΑ
ΔI_{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other pins at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
Cı	input capacitance		-	3	10	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 10.

Symbol	Parameter	Conditions		25 °C		-40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	Min	Max	_
74AHC1	64-Q100	1				ı		I		
t _{pd}	propagation	CP to Qn; see Figure 7	<u>?]</u>							
	delay	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C _L = 15 pF	-	6.5	12.8	1.0	15.0	1.0	16.0	ns
		$C_L = 50 \text{ pF}$	-	9.3	16.3	1.0	18.5	1.0	20.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		C _L = 15 pF	-	4.5	9.0	1.0	10.5	1.0	11.5	ns
		$C_L = 50 \text{ pF}$	-	6.4	11.0	1.0	12.5	1.0	14.0	ns
		MR to Qn; see Figure 8	<u>B]</u>							
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C _L = 15 pF	-	5.3	12.8	1.0	15.0	1.0	16.0	ns
		$C_L = 50 \text{ pF}$	-	7.6	16.3	1.0	18.5	1.0	20.5	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		C _L = 15 pF	-	4.0	8.6	1.0	10.0	1.0	11.0	ns
		$C_L = 50 \text{ pF}$	-	5.8	10.6	1.0	12.0	1.0	13.5	ns
f _{max}	maximum	see Figure 7								
	frequency	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$								
		C _L = 15 pF	80	125	-	65	-	50	-	MHz
		$C_L = 50 \text{ pF}$	50	75	-	45	-	35	-	MHz
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$								
		C _L = 15 pF	125	175	-	105	-	85	-	MHz
		$C_L = 50 \text{ pF}$	85	115	-	75	-	65	-	MHz
t _W	pulse width	CP HIGH or LOW; see Figure 7								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
t_{WL}	pulse width	MR; see Figure 8								
	LOW	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	DSA, DSB to CP; see Figure 9								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	5.0	-	-	6.0	-	6.0	-	ns
		V _{CC} = 4.5 V to 5.5 V	4.5	-	-	4.5	-	4.5	-	ns
t _h	hold time	DSA, DSB to CP; see Figure 9								
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.5	-	-	1.5	-	1.5	-	ns
		V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	ns

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 Table 7.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 10.

Symbol	Parameter	Conditions			25 °C		–40 °C	to +85 °C	–40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	Min	Max	
t _{rec}	recovery	MR to CP; see Figure 8									
	time	$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.5	-	-	2.5	-	2.5	-	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		2.5	-	-	2.5	-	2.5	-	ns
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[4]	-	48	-	-	-	-	-	pF
74AHCT	164-Q100; V _C	_C = 4.5 V to 5.5 V									
t _{pd}		CP to Qn; see Figure 7	[2]								
	delay	C _L = 15 pF		-	3.4	9.0	1.0	10.5	1.0	11.5	ns
		C _L = 50 pF		-	4.9	11.0	1.0	12.5	1.0	14.0	ns
		MR to Qn; see Figure 8	[3]								
		C _L = 15 pF		-	3.5	8.6	1.0	10.0	1.0	11.0	ns
		C _L = 50 pF		-	5.0	10.6	1.0	12.0	1.0	13.5	ns
f_{max}	maximum	see Figure 7									
	frequency	$C_L = 15 pF$		125	175	-	105	-	85	-	MHz
		$C_L = 50 \text{ pF}$		85	115	-	75	-	65	-	MHz
t_{W}	pulse width	CP HIGH or LOW; see Figure 7		5.0	-	-	5.0	-	5.0	-	ns
t_{WL}	pulse width LOW	MR; see Figure 8		5.0	-	-	5.0	-	5.0	-	ns
t _{su}	set-up time	DSA, DSB to CP; see Figure 9		4.5	-	-	4.5	-	4.5	-	ns
t _h	hold time	DSA, DSB to CP; see Figure 9		2.0	-	-	2.0	-	2.0	-	ns
t _{rec}	recovery time	MR to CP; see Figure 8		2.5	-	-	2.5	-	2.5	-	ns
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$	[4]	-	51	-	-	-	-	-	pF

^[1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o) \text{ where:}$

 f_i = input frequency in MHz;

 f_0 = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

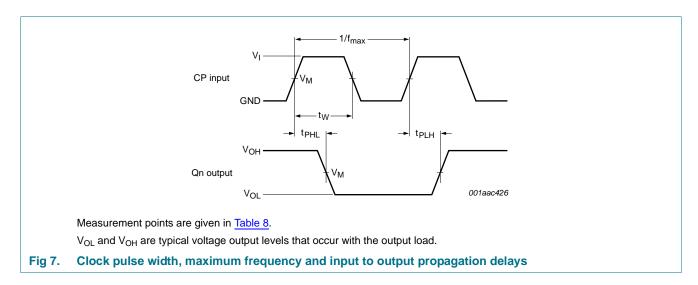
 $\Sigma (C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

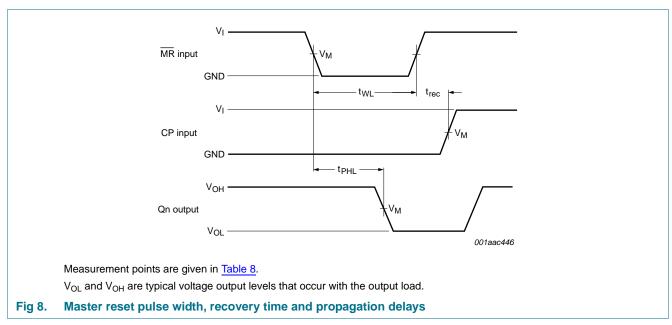
^[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

^[3] t_{pd} is the same as t_{PHL} only.

^[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

11. Waveforms





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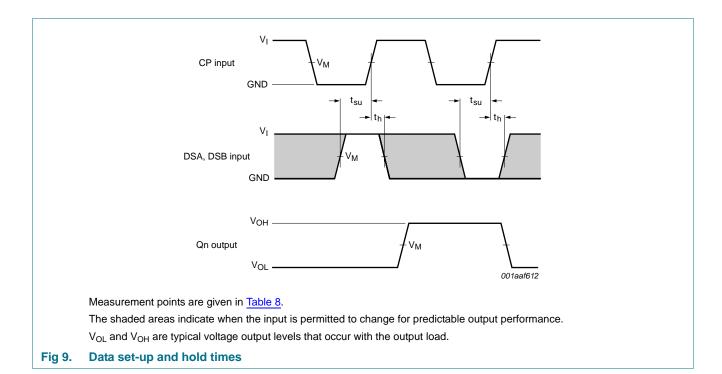
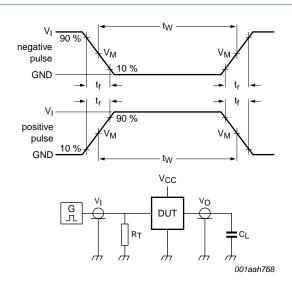


Table 8. Measurement points

Туре	Input	Output		
	V _M	V _M		
74AHC164-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$		
74AHCT164-Q100	1.5 V	$0.5 \times V_{CC}$		

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Test data is given in Table 9.

Definitions test circuit:

 R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator

 C_L = Load capacitance including jig and probe capacitance

Fig 10. Load circuitry for measuring switching times

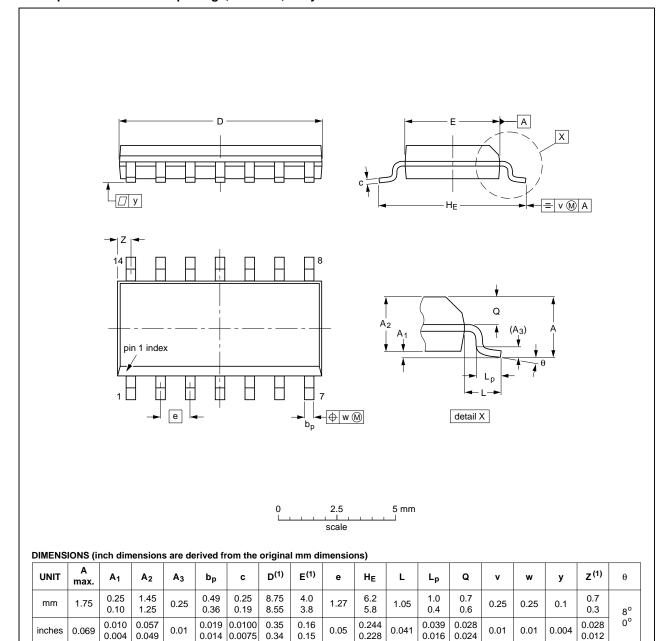
Table 9. Test data

Туре	Input L		Load	Test	
	VI	t _r , t _f	CL		
74AHC164-Q100	V _{CC}	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}	
74AHCT164-Q100	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}	

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT108-1	076E06	MS-012				99-12-27 03-02-19

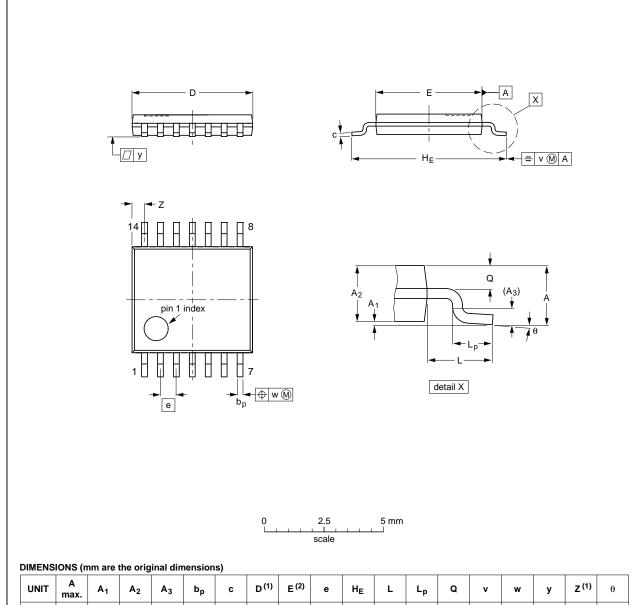
Fig 11. Package outline SOT108-1 (SO14)

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TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT402-1		MO-153				-99-12-27 03-02-18	

Fig 12. Package outline SOT402-1 (TSSOP14)

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DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body 2.5 x 3 x 0.85 mm SOT762-1

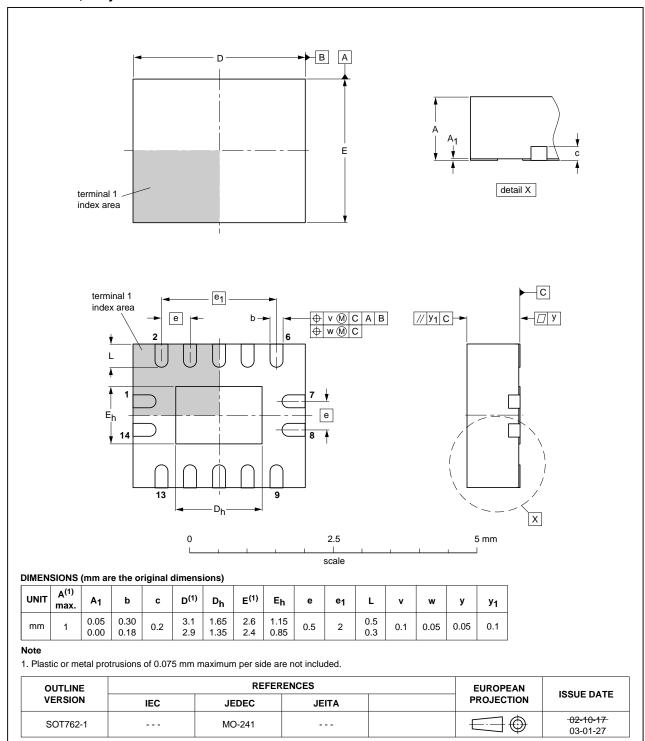


Fig 13. Package outline SOT762-1 (DHVQFN14)

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13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
MIL	Military
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AHC_AHCT164_Q100 v.1	20130705	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition					
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.					
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.					
Product [short] data sheet	Production	This document contains the product specification.					

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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